

# **NPN RF Transistor**

This device is designed for use in low noise UHF/VHF amplifiers, with collector currents in the 100  $\mu A$  to 20 mA range in common emitter or common base mode of operations, and in low frequency drift, high output UHF oscillators. Sourced from Process 42.

### Absolute Maximum Ratings\* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.0	V
I <sub>C</sub>	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		MPSH10	*MMBTH10	
PD	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

\*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# NPN RF Transistor

(continued)

Electrical Characteristics TA = 25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	25		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	30		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	3.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 25 \text{ V}, I_E = 0$		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_{C} = 0$		100	nA
ON CHAR.	ACTERISTICS				
h <sub>FE</sub>	DC Current Gain	$I_{\rm C}$ = 4.0 mA, $V_{\rm CE}$ = 10 V	60		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_{\rm C} = 4.0 \text{ mA}, I_{\rm B} = 0.4 \text{ mA}$		0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_{\rm C} = 4.0 \text{ mA}, V_{\rm CE} = 10 \text{ V}$		0.95	V

## SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C} = 4.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	650		MHz
C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		0.7	pF
C <sub>rb</sub>	Common-Base Feedback Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$	0.35	0.65	pF
rb'C <sub>c</sub>	Collector Base Time Constant	$I_{C} = 4.0 \text{ mA}, V_{CB} = 10 \text{ V},$ f = 31.8 MHz		9.0	pS

\*Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

# **Spice Model**

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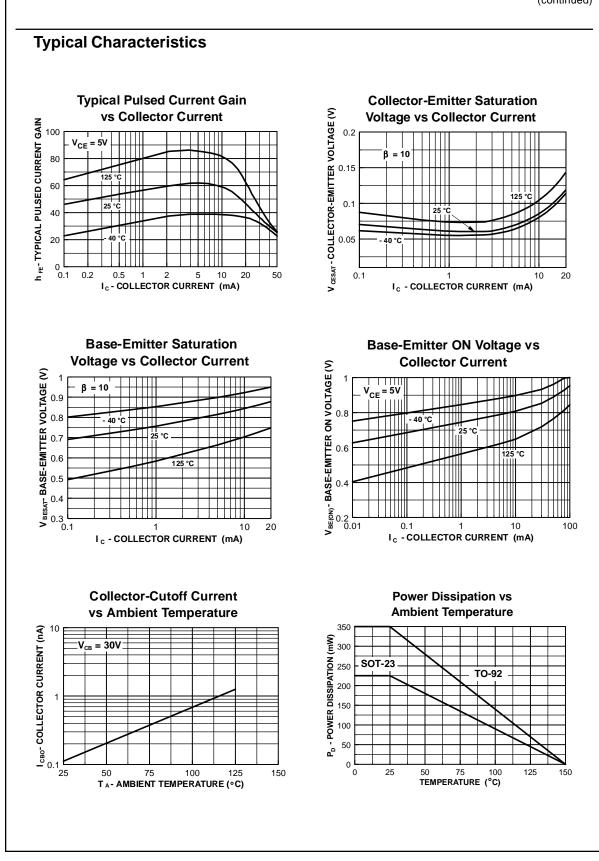
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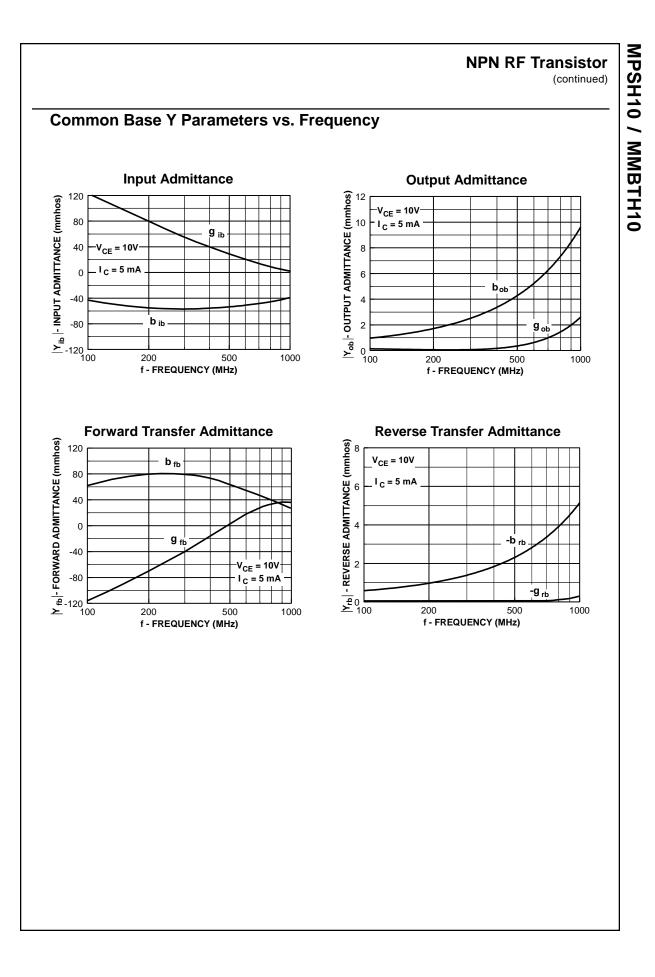
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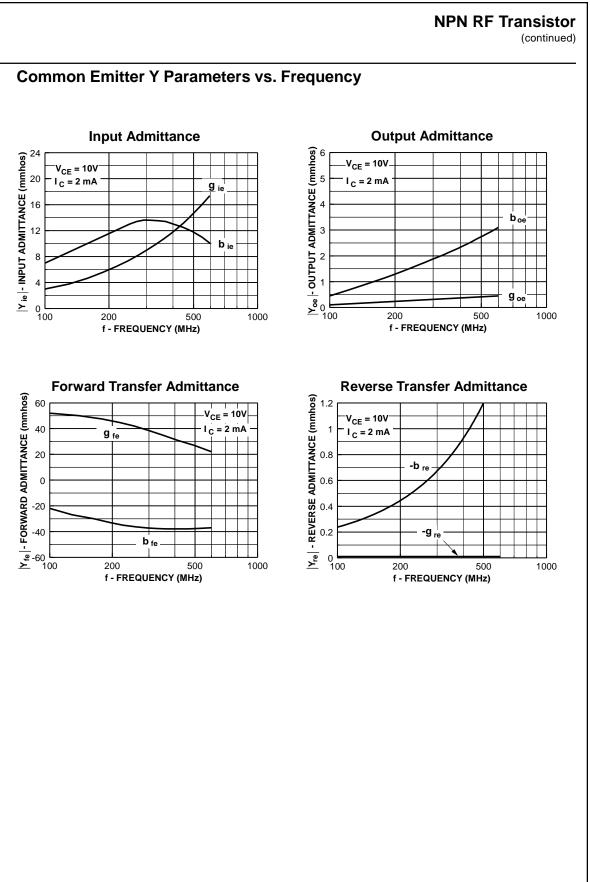
NPN (Is=69.28E-18 Xti=3 Eg=1.11 Vaf=100 Bf=308.6 Ne=1.197 Ise=69.28E-18 Ikf=22.83m Xtb=1.5 Br=1.11 Nc=2 Isc=0 Ikr=0 Rc=4 Cjc=1.042p Mjc=.2468 Vjc=.75 Fc=.5 Cje=1.52p Mje=.3223 Vje=.75 Tr=1.558n Tf=135.8p Itf=.27 Vtf=10 Xtf=30 Rb=10)

NPN RF Transistor (continued)

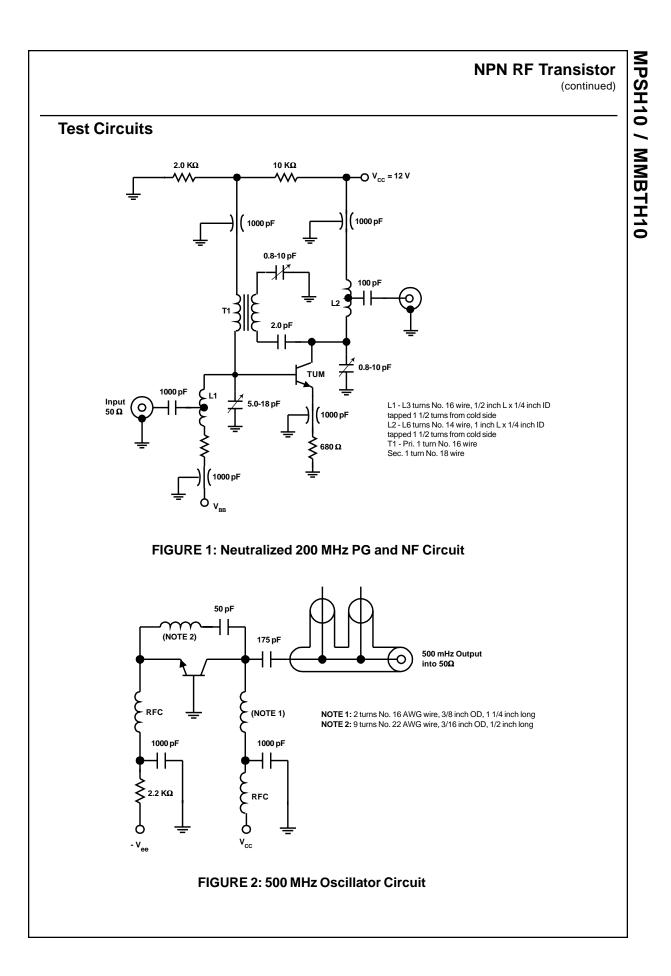
# MPSH10 / MMBTH10







MPSH10 / MMBTH10





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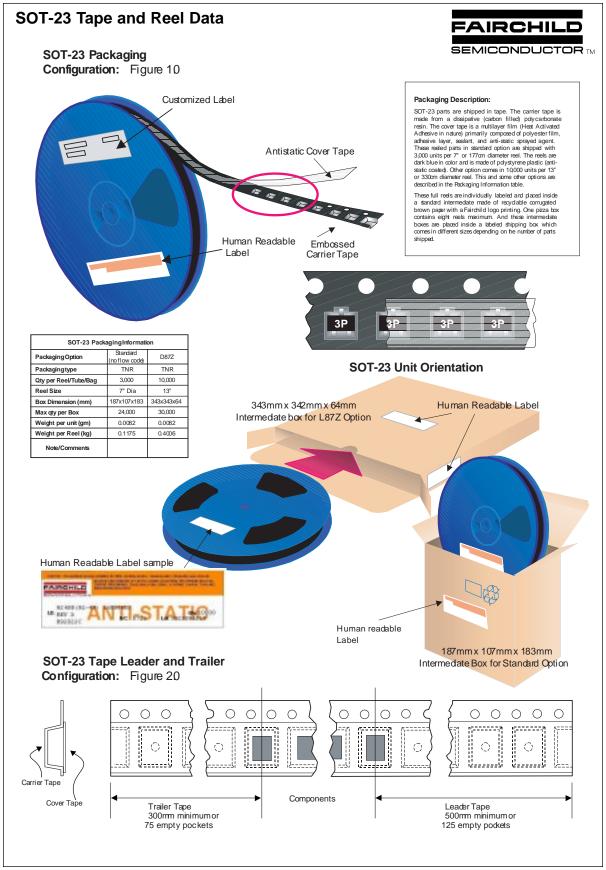
March 2001, Rev. B1





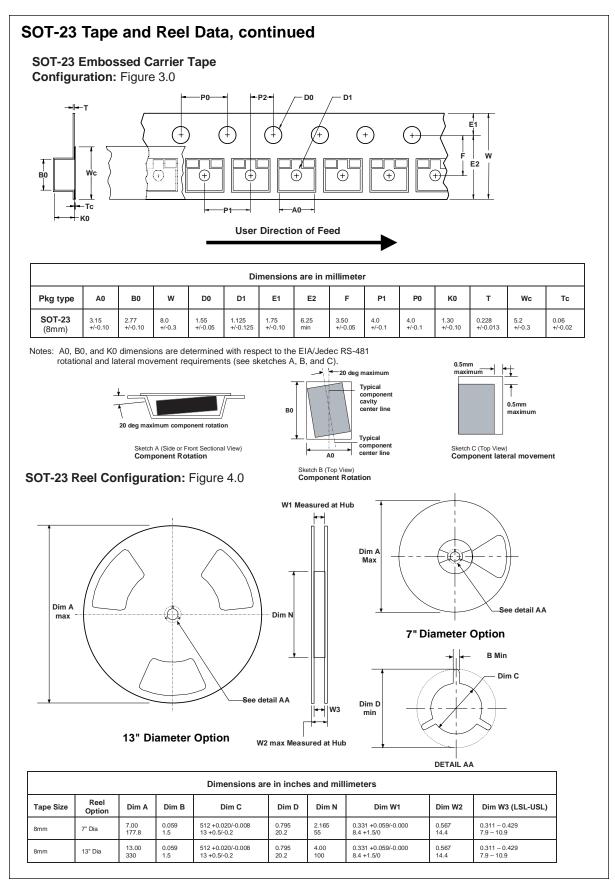
July 1999, Rev. A



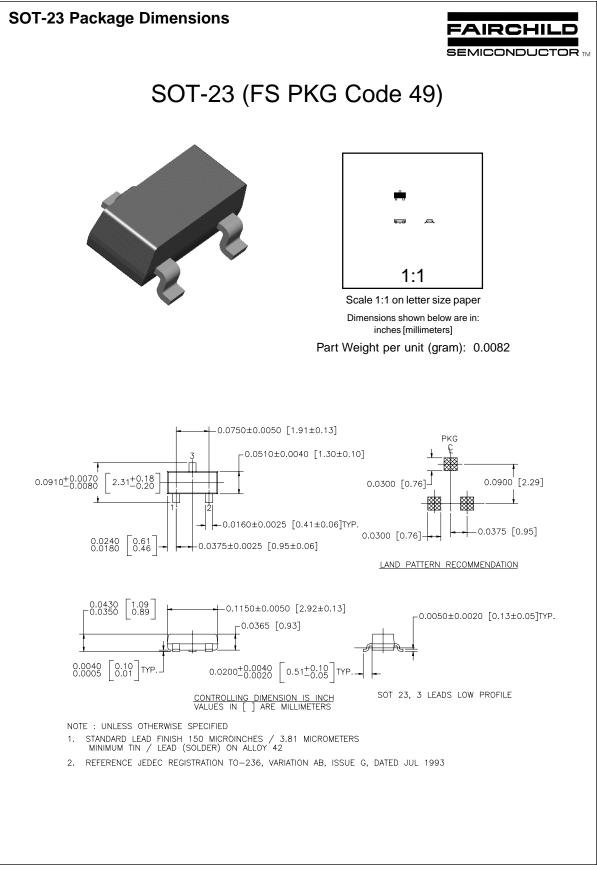


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